

DEC

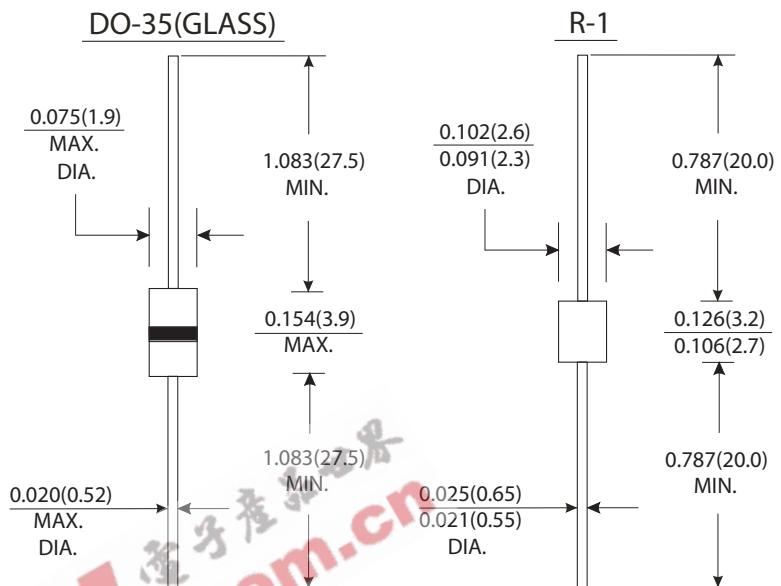
DB3 / DB4

SIGNAL BIDIRECTIONAL
DIAC

Features

The three layer, two terminal, axial lead, hermetically sealed diacs are designed specifically for triggering thyristors. They demonstrate low breakover current at breakover voltage as they withstand peak pulse current. The breakover symmetry is within three volts. These diacs are intended for use in thyristors phase control, circuits for lamp dimming, universal motor speed control, and heat control.

DEC's DB3/DB4 are bi-directional triggered diode designed to operate in conjunction with Triacs and SCR's



Dimensions in inches and (millimeters)

Absolute Ratings (Limiting Values)

Symbols	Parameters	Value		Units	
		DB3	DB4		
P _c	Power Dissipation on Printed Circuit(L=10mm)	TA=50 °C	150	mW	
I _{TRM}	Repetitive Peak on-state Current	t _p =10 μs F=100Hz	2.0	2.0	A
T _{STG/TJ}	Storage and Operating Junction Temperature	-40 to +125/-40 to 110		°C	

Electrical characteristics

Symbols	Parameters	Test Conditions	Value		Units
			DB3	DB4	
V _{BO}	Breakover Voltage (Note 2)	C=22nF(Note2) See diagram 1	Min	28	V
			Typ	32	
			Max	36	
+V _{BO} - -V _{BO}	Breakover Voltage Symmetry	C=22nF(Note2) See diagram 1	Max	± 3	V
± ΔV	Dynamic Breakover Voltage (Note 1)	△I=(I _{BO} to I _F =10mA) See diagram 1	Min	5	V
V _O	Output Voltage (Note 1)	See diagram 2	Min	5	V
I _{BO}	Breakover Current (Note 1)	C=22nF(Note2)	Max	100	μA
t _r	Rise Time (Note 1)	See diagram 3	Typ	1.5	μS
I _B	Leakage Current (Note 1)	V _B =0.5 V _{BO} max see diagram 1	Max	10	μA

Notes:

- (1) Electrical characteristics applicable in both forward and reverse directions
- (2) Connected in parallel with the devices

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RATINGS AND CHARACTERISTIC CURVES DB3/DB4

DIAGRAM 1 : Current-voltage characteristics

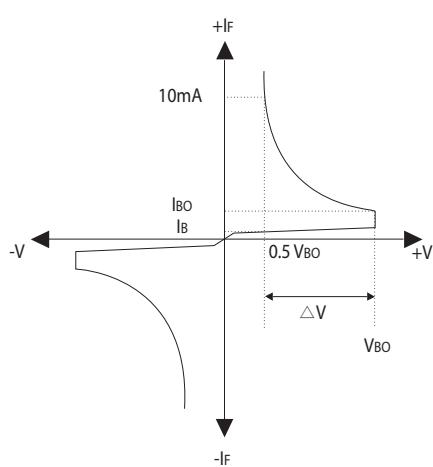


FIG.1-Power dissipation versus ambient temperature (maximum values)

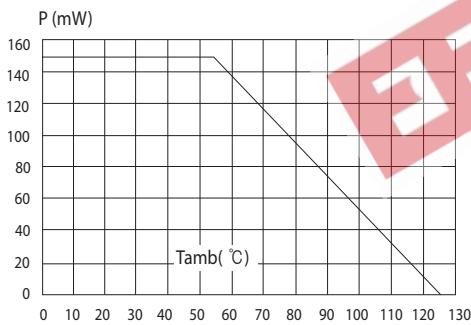


FIG.3-Peak pulse current versus pulse duration (maximum values)

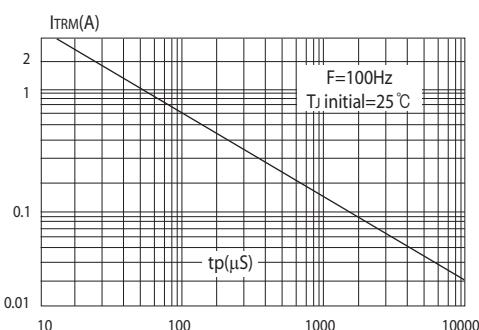


DIAGRAM 2 : Test circuit for output voltage

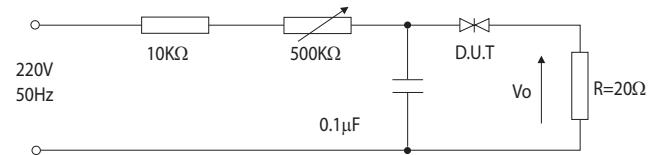


DIAGRAM 3 : Test circuit see diagram2 adjust R for $I_p=0.5\text{A}$

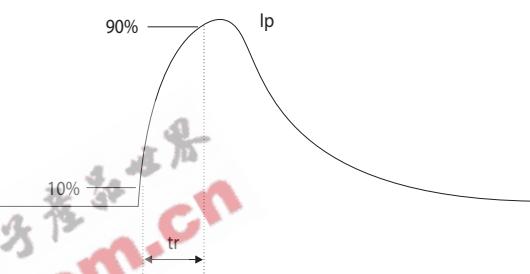


FIG.2-Relative variation of V_{BO} versus junction temperature (typical values)

